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Kind regards,

Team Nexperia

DATA SHEET

For a complete data sheet, please also download:

- The IC04 LOCMOS HE4000B Logic Family Specifications HEF, HEC
- The IC04 LOCMOS HE4000B Logic Package Outlines/Information HEF, HEC

HEF4016B
gates
Quadruple bilateral switches

Product specification
File under Integrated Circuits, IC04

January 1995

Philips Semiconductors

PHILIPS

DESCRIPTION

The HEF4016B has four independent analogue switches (transmission gates). Each switch has two input/output terminals (Y/Z) and an active HIGH enable input (E). When E is connected to V_{DD} a low impedance bidirectional path between Y and Z is established (ON condition). When E is connected to V_{SS} the switch is disabled and a high impedance between Y and Z is established (OFF condition). Current through a switch will not cause additional V_{DD} current provided the voltage at the terminals of the switch is maintained within the supply voltage range; $V_{DD} \geq (V_Y, V_Z) \geq V_{SS}$. Inputs Y and Z are electrically equivalent terminals.

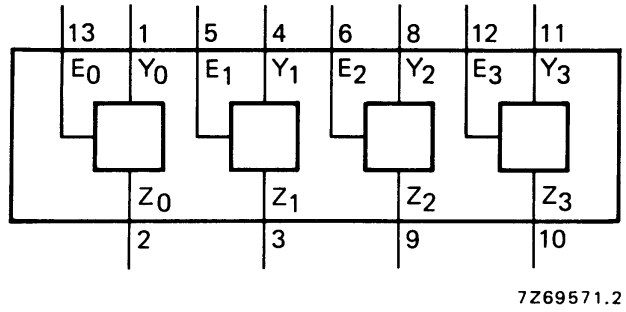


Fig.1 Functional diagram.

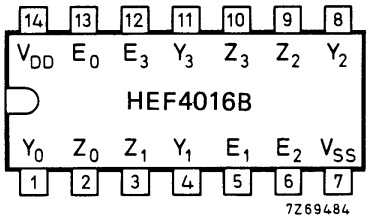


Fig.2 Pinning diagram.

PINNING

E_0 to E_3	enable inputs
Y_0 to Y_3	input/output terminals
Z_0 to Z_3	input/output terminals

HEF4016BP(N): 14-lead DIL; plastic (SOT27-1)
HEF4016BD(F): 14-lead DIL; ceramic (cerdip) (SOT73)
HEF4016BT(D): 14-lead SO; plastic (SOT108-1)
( ): Package Designator North America

APPLICATION INFORMATION

Some examples of applications for the HEF4016B are:

- Signal gating
- Modulation
- Demodulation
- Chopper

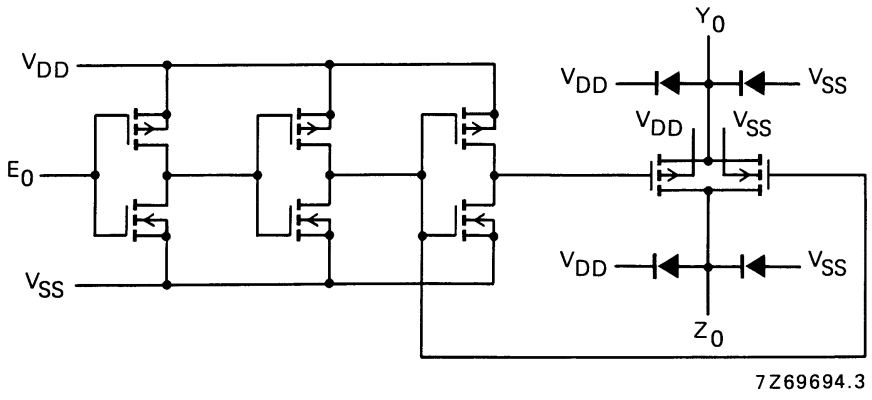


Fig.3 Schematic diagram (one switch).

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Power dissipation per switch	P	max.	100	mW

For other RATINGS see Family Specifications

DC CHARACTERISTICS

T_{amb} = 25 °C; V_{SS} = 0 V (unless otherwise specified)

PARAMETER	V_{DD} V	SYMBOL	TYP.	MAX.	UNIT	CONDITIONS
ON resistance	5	R_{ON}	8000	–	Ω	E_n at V_{IH}; V_{is} = 0 to V_{DD}; see Fig.4
	10		230	690	Ω	
	15		115	350	Ω	
ON resistance	5	R_{ON}	140	425	Ω	E_n at V_{IH}; V_{is} = V_{SS}; see Fig.4
	10		65	195	Ω	
	15		50	145	Ω	
ON resistance	5	R_{ON}	170	515	Ω	E_n at V_{IH}; V_{is} = V_{DD}; see Fig.4
	10		95	285	Ω	
	15		75	220	Ω	
'Δ' ON resistance between any two channels	5	ΔR_{ON}	200	–	Ω	E_n at V_{IH}; V_{is} = 0 to V_{DD}; see Fig.4
	10		15	–	Ω	
	15		10	–	Ω	

PARAMETER	V_{DD} V	SYMBOL	T_{amb} (°C)						UNIT	CONDITION
			−40		+ 25		+ 85			
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
Quiescent device current	5	I_{DD}	–	1,0	–	1,0	–	7,5	μA	V_{SS} = 0; all valid input combinations; V_I = V_{SS} or V_{DD}
	10		–	2,0	–	2,0	–	15,0	μA	
	15		–	4,0	–	4,0	–	30,0	μA	
Input leakage current at E_n	15	± I_{IN}	–	–	–	300	–	1000	nA	E_n at V_{SS} or V_{DD}
OFF-state leakage current, any channel OFF	5	I_{OZ}	–	–	–	–	–	–	nA	E_n at V_{IL}; V_{is} = V_{SS} or V_{DD}; V_{os} = V_{DD} or V_{SS}
	10		–	–	–	–	–	–	nA	
	15		–	–	–	200	–	–	nA	
E_n input voltage LOW	5	V_{IL}	–	1,5	–	1,5	–	1,5	V	switch OFF; see Fig.9 for I_{OZ}
	10		–	3,0	–	3,0	–	3,0	V	
	15		–	4,0	–	4,0	–	4,0	V	
E_n input voltage HIGH	5	V_{IH}	3,5	–	3,5	–	3,5	–	V	low-impedance between Y and Z (ON condition) see R_{ON} switch
	10		7,0	–	7,0	–	7,0	–	V	
	15		11,0	–	11,0	–	11,0	–	V	

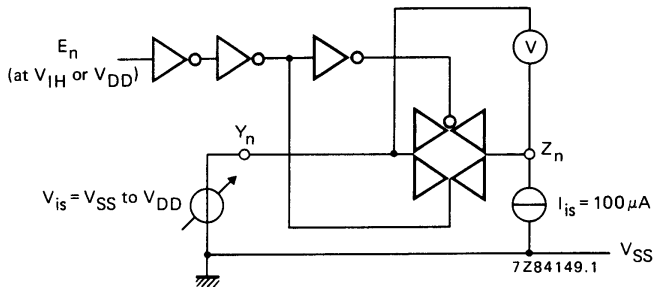
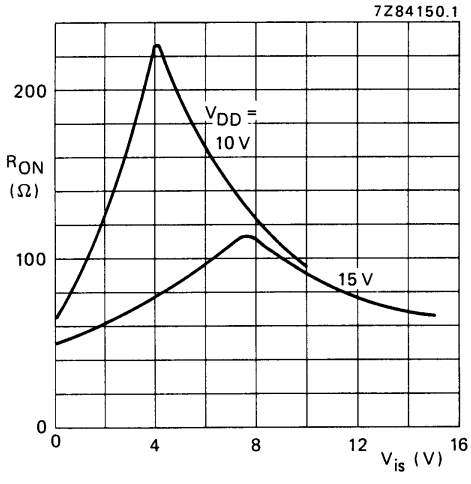


Fig.4 Test set-up for measuring R_{ON}.



$E_n > V_{IH}$
I_{is} = 100 μA
V_{SS} = 0 V

Fig.5 Typical R_{ON} as a function of input voltage.

AC CHARACTERISTICS

V_{SS} = 0 V; T_{amb} = 25 °C; input transition times ≤ 20 ns

	V_{DD} V	SYMBOL	TYP.	MAX.		
Propagation delays						
$V_{is} \rightarrow V_{os}$	5		25	50	ns	
HIGH to LOW	10	t_{PHL}	10	20	ns	note 1
	15		5	10	ns	
	5		20	40	ns	
LOW to HIGH	10	t_{PLH}	10	20	ns	note 1
	15		5	10	ns	
Output disable times						
$E_n \rightarrow V_{os}$	5		90	130	ns	
HIGH	10	t_{PHZ}	80	110	ns	note 2
	15		75	100	ns	
	5		85	120	ns	
LOW	10	t_{PLZ}	75	100	ns	note 2
	15		75	100	ns	
Output enable times						
$E_n \rightarrow V_{os}$	5		40	80	ns	
HIGH	10	t_{PZH}	20	40	ns	note 2
	15		15	30	ns	
	5		40	80	ns	
LOW	10	t_{PZL}	20	40	ns	note 2
	15		15	30	ns	
Distortion, sine-wave	5		–		%	
response	10		0,08		%	note 3
	15		0,04		%	
Crosstalk between	5		–		MHz	
any two channels	10		1		MHz	note 4
	15		–		MHz	
Crosstalk; enable	5		–		mV	
input to output	10		50		mV	note 5
	15		–		mV	
OFF-state	5		–		MHz	
feed-through	10		1		MHz	note 6
	15		–		MHz	
ON-state frequency	5		–		MHz	
response	10		90		MHz	note 7
	15		–		MHz	

Notes

V_{is} is the input voltage at a Y or Z terminal, whichever is assigned as input.

V_{os} is the output voltage at a Y or Z terminal, whichever is assigned as output.

1. R_L = 10 kΩ to V_{SS}; C_L = 50 pF to V_{SS}; $E_n = V_{DD}$; $V_{is} = V_{DD}$ (square-wave); see Figs 6 and 10.
2. R_L = 10 kΩ; C_L = 50 pF to V_{SS}; $E_n = V_{DD}$ (square-wave);
   $V_{is} = V_{DD}$ and R_L to V_{SS} for t_{PHZ} and t_{PZH};
   $V_{is} = V_{SS}$ and R_L to V_{DD} for t_{PLZ} and t_{PZL}; see Figs 6 and 11.
3. R_L = 10 kΩ; C_L = 15 pF; $E_n = V_{DD}$; $V_{is} = \frac{1}{2}V_{DD(p\text{-}p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);
   f_{is} = 1 kHz; see Fig.7.
4. R_L = 1 kΩ; $V_{is} = \frac{1}{2}V_{DD(p\text{-}p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

   $20 \log \frac{V_{os}(B)}{V_{is}(A)} = -50$ dB; E_n (A) = V_{SS}; E_n (B) = V_{DD}; see Fig. 8.
5. R_L = 10 kΩ to V_{SS}; C_L = 15 pF to V_{SS}; $E_n = V_{DD}$ (square-wave); crosstalk is $|V_{os}|$ (peak value);
   see Fig.6.
6. R_L = 1 kΩ; C_L = 5 pF; $E_n = V_{SS}$; $V_{is} = \frac{1}{2}V_{DD(p\text{-}p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

   $20 \log \frac{V_{os}}{V_{is}} = -50$ dB; see Fig. 7.
7. R_L = 1 kΩ; C_L = 5 pF; $E_n = V_{DD}$; $V_{is} = \frac{1}{2}V_{DD(p\text{-}p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

   $20 \log \frac{V_{os}}{V_{is}} = -3$ dB; see Fig. 7.

	V_{DD} V	TYPICAL FORMULA FOR P (μW)	
Dynamic power dissipation per package (P)[1]	5	$550 f_i + \sum (f_o C_L) \times V_{DD}^2$	where
	10	$2\,600 f_i + \sum (f_o C_L) \times V_{DD}^2$	f_i = input freq. (MHz)
	15	$6\,500 f_i + \sum (f_o C_L) \times V_{DD}^2$	f_o = output freq. (MHz)
			C_L = load capacitance (pF)
			$\sum (f_o C_L)$ = sum of outputs
			V_{DD} = supply voltage (V)

Note

1. All enable inputs switching.

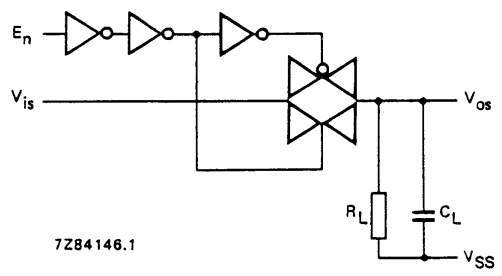


Fig.6

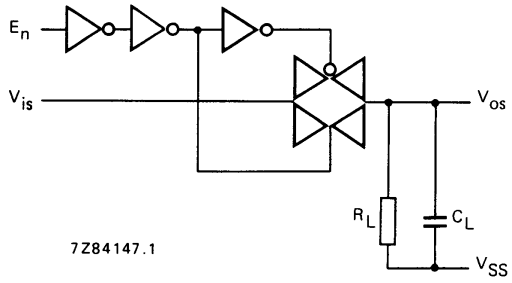


Fig.7

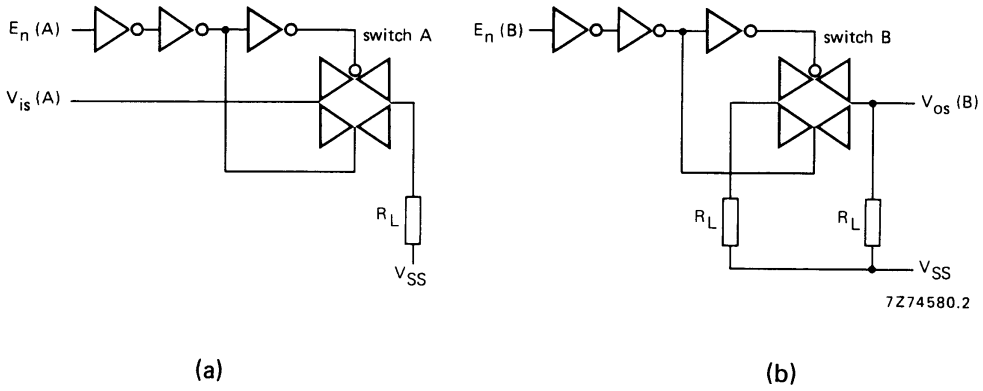


Fig.8

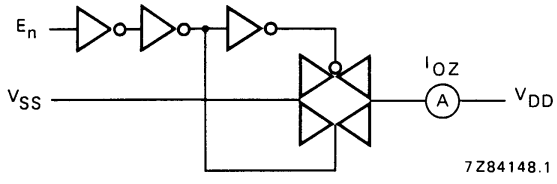


Fig.9

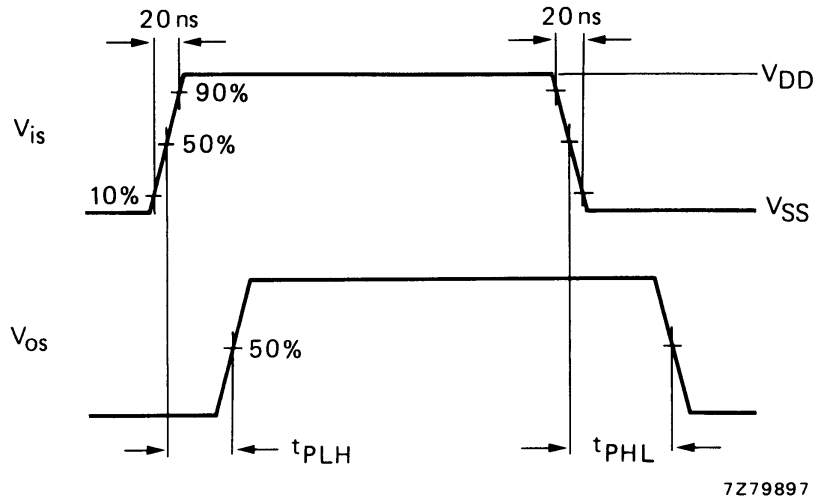
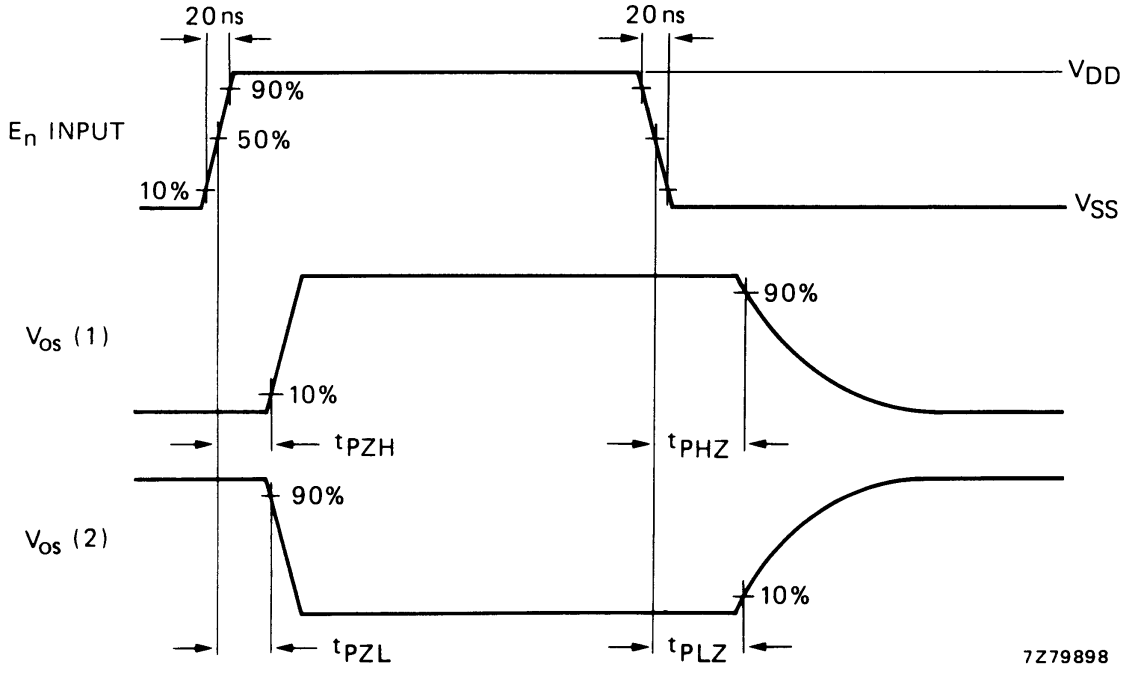


Fig.10 Waveforms showing propagation delays from V_{is} to V_{os}.



(1) V_{is} at V_{DD}
(2) V_{is} at V_{SS}

Fig.11 Waveforms showing output disable and enable times.